

In The Specification

Paragraph beginning at line 12 of page 6 has been amended
as follows:

b - It is yet another further object of the present invention to provide a wafer pedestal that is effective in cooling a high temperature processed wafer that includes a pedestal that has a grooved surface including at least five circular grooves concentrically formed in the top surface and three linear grooves formed in radial directions emanating from a center of the top surface. -

Paragraph beginning at line 7 of page 11 has been amended
as follows:

B - In the novel cooling stage, the first plurality of circular grooves provided is at least three, and preferably at least five, while the second plurality of grooves provided is at least two, and preferably at least

three. The dimensions of the grooves provided may be a width between about 1 mm and about 7 mm, and a depth between about 1 mm and about 7 mm, preferably a width between about 3 mm and about 5 mm, and a depth between about 1 mm and about 3 mm. The novel cooling stage may be advantageously situated in a cool-down chamber as part of a cluster tool for sputtering metal on a semiconductor wafer. The cooling stage may be advantageously used between a high temperature sputtering process and a low temperature sputtering process for the rapid and uniform cooling of a wafer from a high process temperature, i.e., 300°C, which is frequently encountered in the sputtering of an aluminum/copper alloy. -
